Ordering number: EN 1546B

SANYO

No.1546B

2SC3448

NPN Triple Diffused Planar Silicon Transistor

500V/4A Switching Regulator Applications

Use

. Switching regulator

Features

- High breakdown voltage and high reliability
- Fast switching speed (tf: 0.1μs typ.)
- Wide ASO
- Adoption of MBIT process

Absolute Maximum Ratings at Ta=25°C

				unit
Collector-to-Base Voltage	V_{CBO}		800	V
Collector-to-Emitter Voltage	V_{CEO}		500	V
Emitter-to-Base Voltage	V_{EBO}		7	V
Collector Current	I_C		4	A
Collector Current (Pulse)	I_{CP}	PW≦300μs, Duty Cycle≦10%	8	A
Base Current	I_B		1.5	A
Collector Dissipation	P_C	T_C=25°C	60	W
Junction Temperature	T_j		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

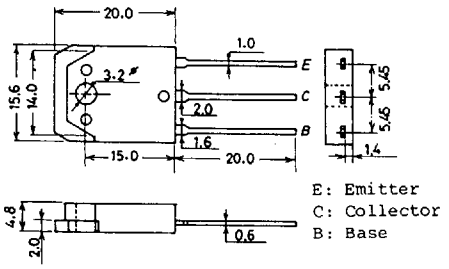
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	V_{CB}=500V, I_E=0			10	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=5V, I_C=0			10	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=5V, I_C=0.3A	15*		50*	
	$h_{FE(2)}$	V_{CE}=5V, I_C=1.5A	8			
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=0.3A		18		MHz
Output Capacitance	**Cob**	V_{CB}=10V, f=1MHz		50		pF
C-E Saturation Voltage	$V_{CE(sat)}$	I_C=1.5A, I_B=0.3A			1.0	V
B-E Saturation Voltage	$V_{BE(sat)}$	I_C=1.5A, I_B=0.3A			1.5	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	I_C=1mA, I_E=0	800			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C=5mA, R_{BE}=∞	500			V
E-B breakdown Voltage	$V_{(BR)EBO}$	I_E=1mA, I_C=0	7			V

*: The $h_{FE(1)}$ of the 2SC3448 is classified as follows. When specifying the $h_{FE(1)}$ rank, specify two ranks or more in principle.

15 L 30	20 M 40	30 N 50

Continued on next page.

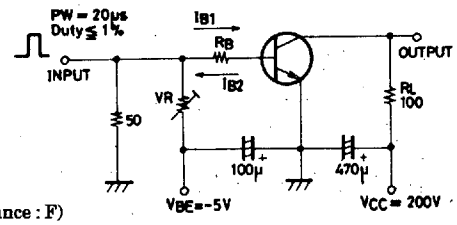
Package Dimensions 2022
(unit:mm)



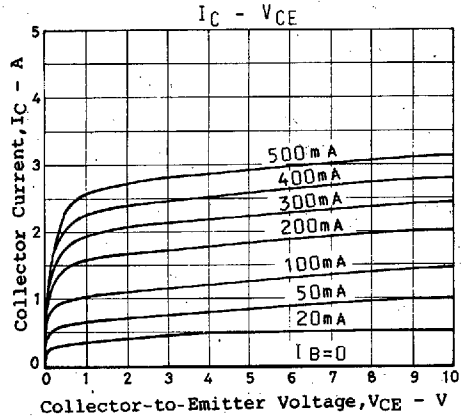
SANYO Electric Co.,Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg.,1-10,1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

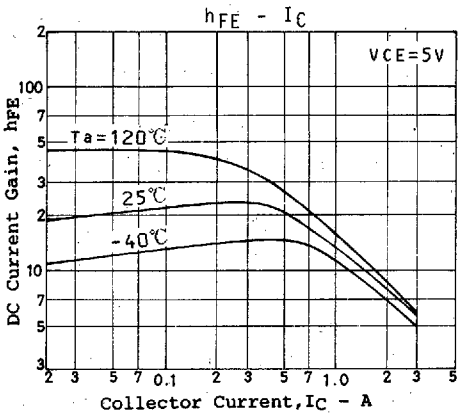
Continued from preceding page.			min	typ	max	unit
C-E Sustain Voltage	$V_{CEX(sus)}$	I_C=1.5A I_{B1}=-I_{B2}=0.6A, L=1mH, clamped	500			V
Turn-on Time	t_{on}	V_{CC}=200V, 5I_{B1}=-2.5I_{B2}=I_C=2A, R_L=100Ω			0.5	μs
Storage Time	t_{stg}				3.0	μs
Fall Time	t_f				0.3	μs

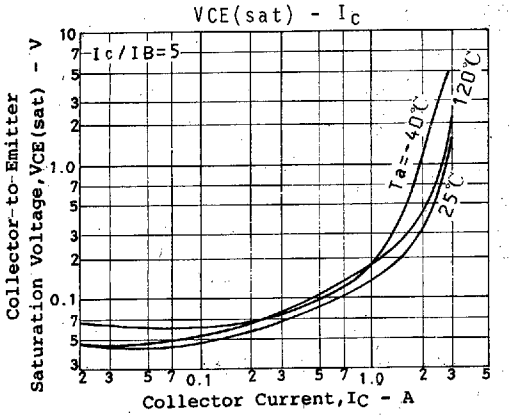
Switching Time Test Circuit

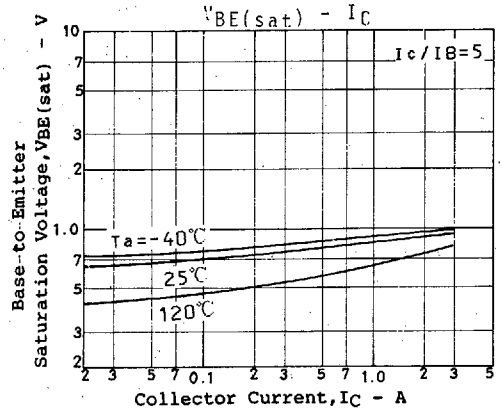


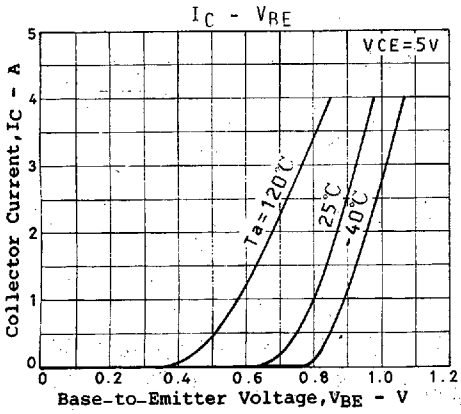
Unit (Resistance : Ω, Capacitance : F)

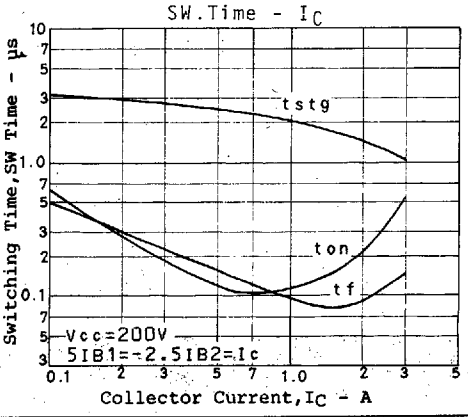




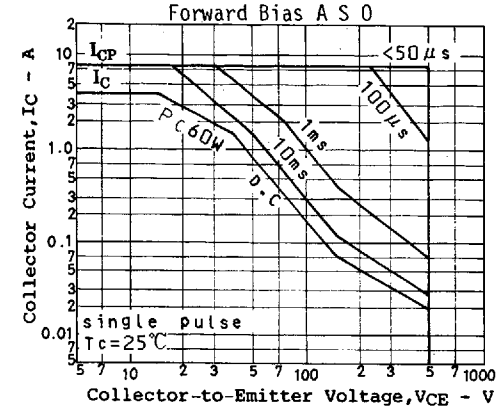








Forward Bias A S O



Reverse Bias A S O